

Abstract:**Method for Producing a Single Crystal of Semiconductor Material**

5 The invention relates to a method for producing a single
crystal of semiconductor material, comprising the melting of
semiconductor material granules by means of a first induction
heating coil on a dish with a run-off tube consisting of the
semiconductor material, the formation of a melt of molten
10 granules, which extends from the run-off tube in the form of a
melt neck and a melt waist to a phase boundary, the delivery
heat to the melt by means of a second induction heating coil,
which has an opening through which the melt neck passes,
crystallization of the melt at the phase boundary, and the
15 delivery of a cooling gas to the run-off tube and to the melt
neck, in order to control the axial position of an interface
between the run-off tube and the melt neck. The invention also
relates to a device for carrying out the method.

Fig. 1